



Silicon-organic hybrid electro-optic modulators for next generation optical interconnects A. Mertens, SilOriX GmbH



SilOriX: Mission & Vision

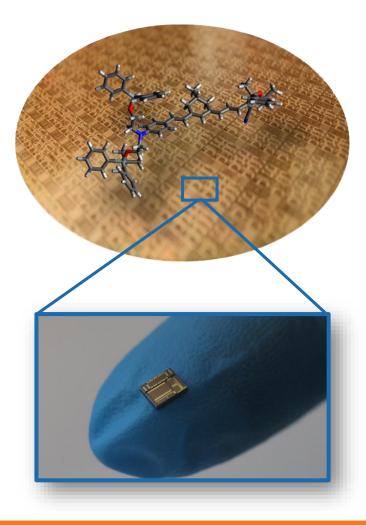


Mission

SilOriX delivers components for energy-efficient electrooptic conversion of signals in high-speed communication networks. Our mission is to provide scalable and sustainable solutions by enhancing silicon photonics through engineered organic materials.

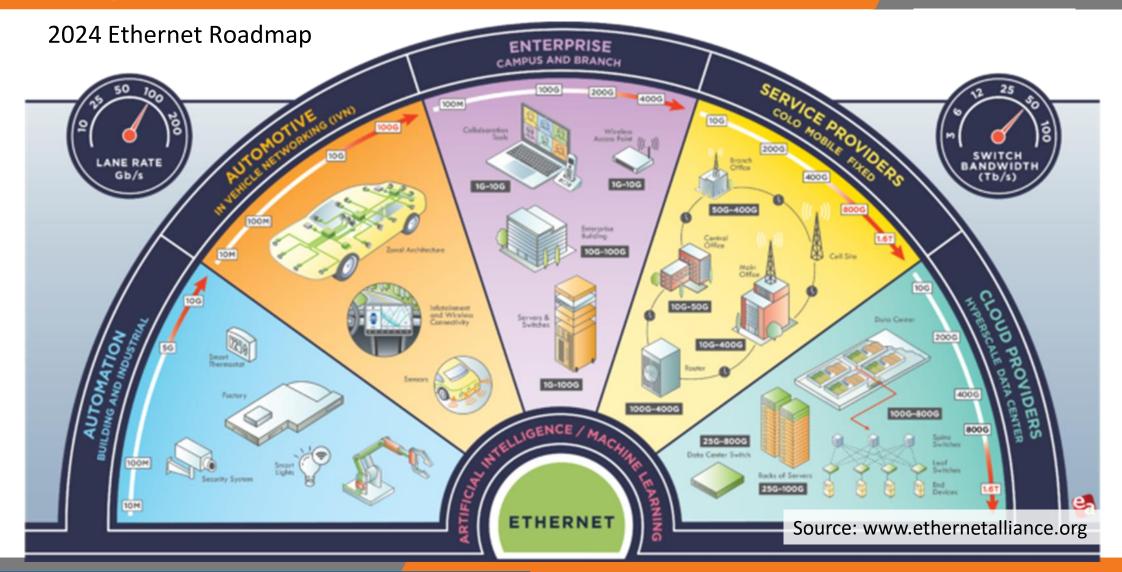
Vision

SilOriX will become the technology leader and global supplier of silicon-organic hybrid (SOH) photonic integrated circuits (PIC).



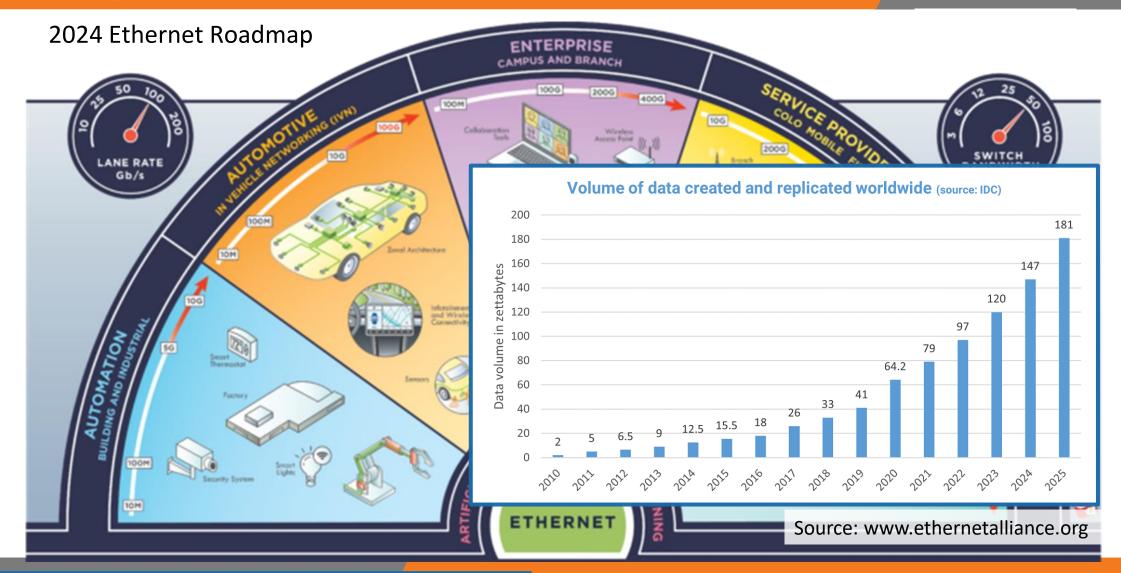
Application pull: Scalable optical communication networks





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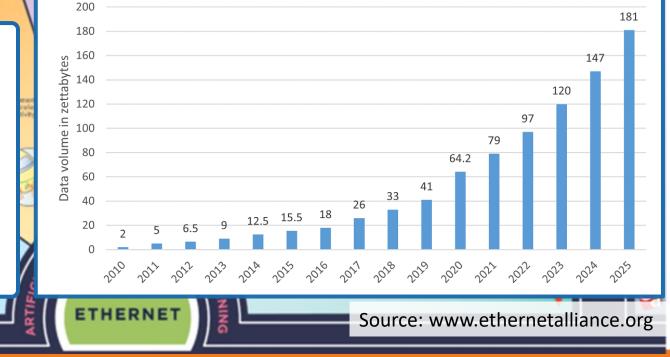




Needed: Compact high-speed optical transceivers

- High symbol rates: 50 GBd, 100 GBd, 130 GBd ...
- Higher-order modulation formats: PAM4, PAM8, 16QAM, 32QAM ...
- Parallelization of lanes in small packages: Modulators with low $U_{\pi}L$
- Cost-efficient mass production mandatory

Volume of data created and replicated worldwide (source: IDC)



Technology push: Silicon photonics

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Silicon photonics:

- High integration density
- Mature CMOS technology Large-scale photonic-electronic integration with high yield
- Ecosystem of foundries
 Fabless fabrication: Shared investment and development costs

Technology push: Silicon photonics

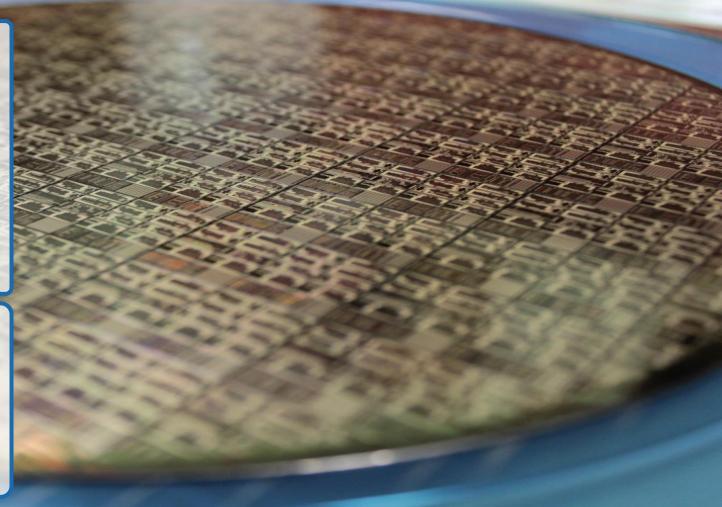


Silicon photonics:

- High integration density
- Mature CMOS technology Large-scale photonic-electronic integration with high yield
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Silicon modulators

- Power hungy
- Bulky in size
- Limited in speed



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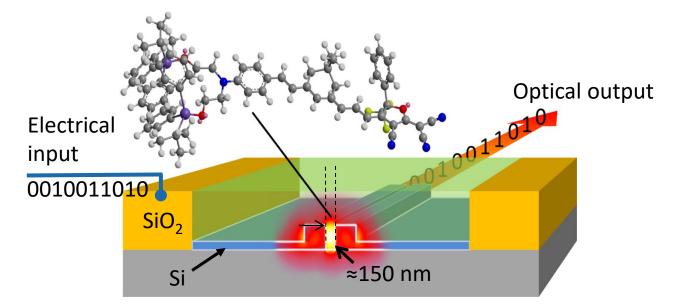
Silicon modulators

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- Bulky in size
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Electro-optic molecules

- Material-efficient solution processes (e.g. inkjet printing)
- High-performance (r₃₃ beyond 100 pm/V)
- Tailor-made materials for various applications

SOH Technology: Performance

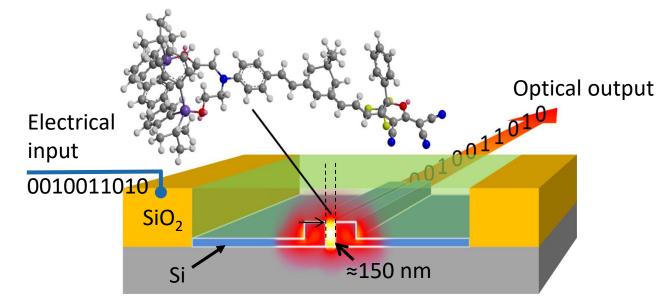


Concept: Combine silicon-on-insulator waveguides with organic electro-optic cladding material

- → High-performance: r_{33} = 390 pm/V, $U_{\pi}L \approx 0.3$ Vmm
- Energy-efficient: < 1 V_{pp}, few fJ/bit for Mach-Zehnder modulator

Wolf *et al.*, Opt. Express **26**, 220-232 (2018) Kieninger *et al.*, Optica **5**, 739 - 748 (2018) Schwarzenberger et al. OFC 2024, Post-Deadline-Paper Th4B.6

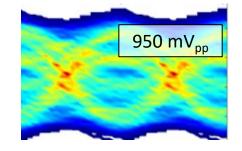
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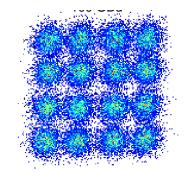
Wolf *et al.*, Opt. Express **26**, 220-232 (2018) Kieninger *et al.*, Optica **5**, 739 - 748 (2018) Schwarzenberger et al. OFC 2024, Post-Deadline-Paper Th4B.6 192 GBd PAM4 (384 Gbit/s)



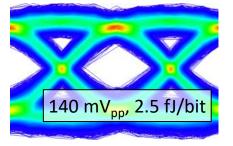
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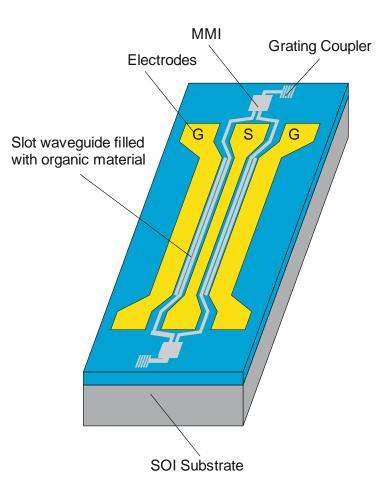
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100 GBd 16 QAM (400 Gbit/s per pol.)

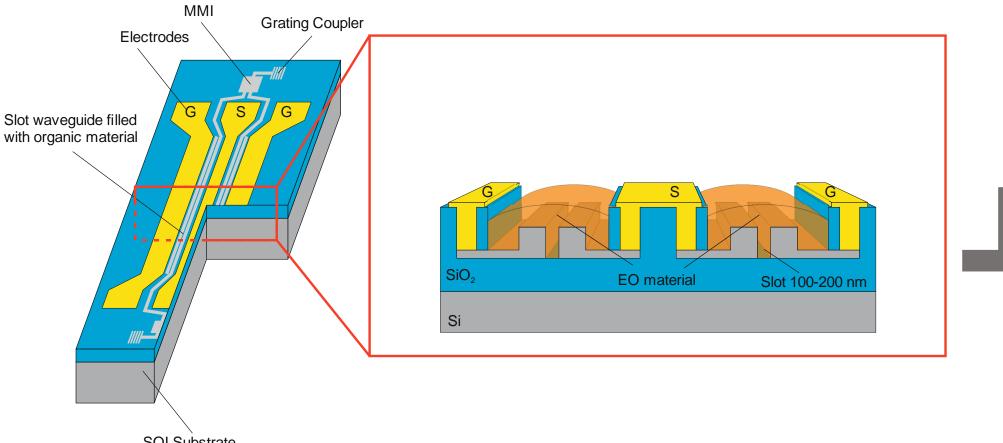


40 Gbit/s OOK





- Basic silicon photonic waveguide structures fabricated in standard silicon photonic process along with full portfolio of other devices (SiGe detectors *etc.*)
 ⇒ High integration density, high yield
- Organic EO materials deposited and poled in a backend post-processing step
 ⇒ No compatibility conflicts with front-end CMOS processing



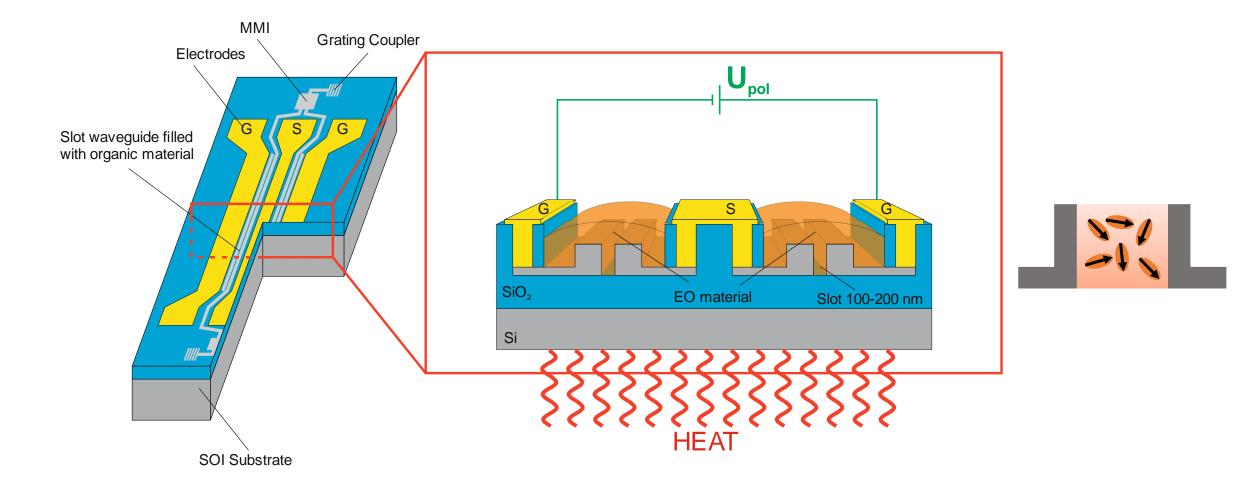
SOI Substrate

Proprietary and Confidential

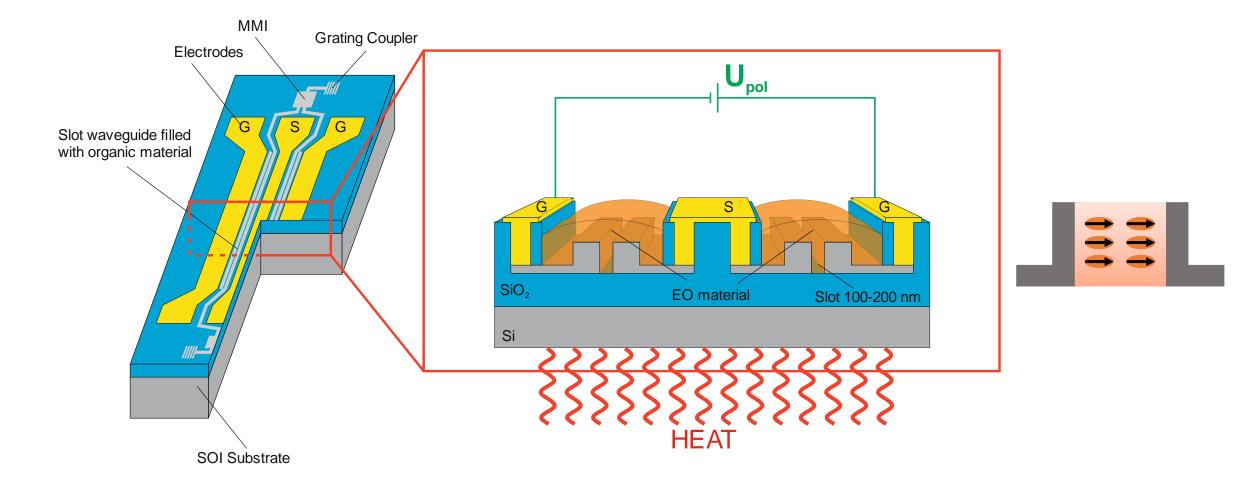
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Slot waveguide filled with organic material

SiO₂

Si

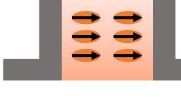
Grating Coupler

Core Technology: Silicon-Organic Hybrid (SOH) Integration



EO material

Slot 100-200 nm



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SOI Substrate

MMI

Electrodes



SilOriX

Low drive-voltage hybrid silicon photonic modulator Tentative specifications

General description

- Pockels-effect Mach-Zehnder modulator (MZM) or IQ modulator exploiting silicon-organic hybrid (SOH) technology
- Intensity modulation and direct detection (IMDD) @ ≥ 56 Gbd PAM4 (≥ 112 Gbit/s/λ)
- Coherent transmission @ ≥ 64 Gbd 64 QAM (≥ 960 Gbit/s/λ using
- polarization multiplexing) • Low drive voltage (≤ 1 V_{pp}) and small foot print (≤ 1 mm)
- DC bias adjusted via separate contacts
- Monolithic co-integration with full portfolio of silicon photonic building blocks Cost-efficient scalability to large-scale production

Applications

- Transceivers for datacom and telecom
- Power-efficient n × 200 Gbit/s (n = 4, 8, 16 ...) IMDD links for data center and campus area networks Coherent data center interconnects (DCI)
- Massively parallel wavelength division multiplexing (WDM)
- Measurement and test equipment for high-speed communications
- Microwave photonics
- Croygenic Transceivers (T = 4 K)
- 🗿 🙆 🍪

M7M

Fig. 1 (a) Micrograph of an array of silicon-organic hybrid (SOH) MZM, (b) and (c) Generated 16 QAM constellation diagrams using an SOH IQ modulator at symbol rates of 50 and 80 GBd.

Specifications for Mach-Zehnder modulator

Standard configuration ¹	Single drive push-pull MZM
DC π-voltage	0.5 1.0 V
Electro-optic bandwidth	≥ 50 GHz @3 dB, ≥ 100 GHz @6 dB
On-chip optical loss	≤ 2 dB
DC extinction ratio	≥ 30 dB
Operating wavelengths	1250 nm 1450 nm
	1350 nm 1550 nm
	1450 nm 1650 nm
On-chip device footprint	≤ 1000 µm x 200 µm (modulator only)
	≤ 1300 µm x 300 µm (including contact pads)
π-voltage-length product	0.5 1.0 Vmm
Chirp parameter	≤0.1
RF impedance	50 Ω
Operating temperature ²	-270 °C - 85 °C
Maximum optical input power	15 dBm

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Further information

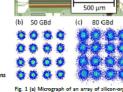
C. Koos et al., "Silicon-Organic Hybrid (20H) and Plasmonic-Organic Hybrid (POH) integration," J. Lightw. Technol. 34, 235–288 (2015).
S. Wolf et al., "Silicon-Organic Hybrid (20H) Machine Zeinder Modulators for 100 Goldy on-off Keying," Sci. Rep. 8, 2358 (2013).
S. Wolf et al., "Cherent modulation up to 100 Gold 150,2M using Siliconorganic hybrid (SOH) devices," Opt. Express 26, 220-232 (2018).

 H. Zwickel et al., "Silicon-organic hybrid (SOH) modulators for intensity-modulation / direct-detection links with line rates of up to 120 Gbit/s," Opt. Express 25, 23784-23800 (2017). to Lordon, Y., Oyi, Explose S, S/Am-SS60 (2017) C. Kleiniger et al., "Ultra-file lector-optic activity demonstrated in a silicon-organic hybrid modulator," Optica 5, 739–748 [2015]. C. Kleiniger et al., "Demonstration of Long-Term Therma Stability of a Silicon-Organic Hybrid (SOH) Modulator et 83°C," arXiv:1807.00774 (hybrid: sOpp)nl (2018).

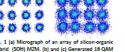
Contact

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¹ Other configurations upon request. Stable operation demonstrated at 85 °C for more than 2500 h.









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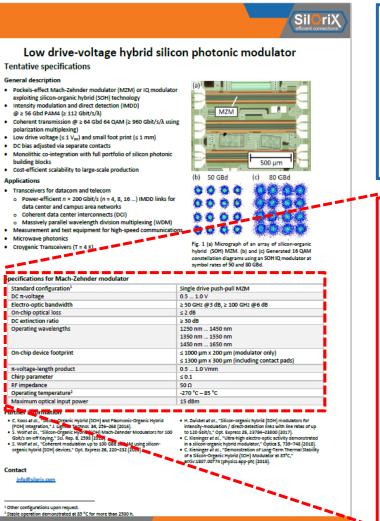


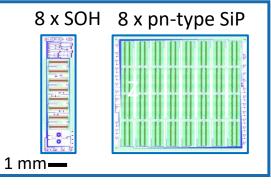
Low drive-voltage hybrid silic	on photonic modulator		
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 Power-efficient n × 200 Gbit/s (n = 4, 8, 16) IMDD links for data center and campus area networks Coherent data center interconnects (DCI) Massively parallel vavelength division multiplexing (WDM) Measurement and test equipment for high-speed communication 			Standard conf
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Croygenic Transceivers (T = 4 K) pecifications for Mach-Zehnder modulator	hybrid (SOH) NZM. (b) and (c) Generated 16 QAM constellation diagrams using an SOH IQ modulator at symbol rates of 50 and 80 GBd.	-	Electro-optic b
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DC π-voltage	0.5 1.0 V
Electro-optic bandwidth	≥ 50 GHz @3 dB, ≥ 100 GHz @6 dB
On-chip optical loss	≤ 2 dB
DC extinction ratio	≥ 30 dB
Operating wavelengths	1260 nm - 1625 nm (O band to L-band)
On-chip device footprint	≤ 1000 μm x 200 μm (modulator only) ≤ 1300 μm x 300 μm (including contact pads)
π-voltage-length product	0.5 1.0 Vmm
Chirp parameter	≤ 0.1
RF impedance	50 Ω
Operating temperature	-270 °C – 85 °C
Maximum optical input power	15 dBm

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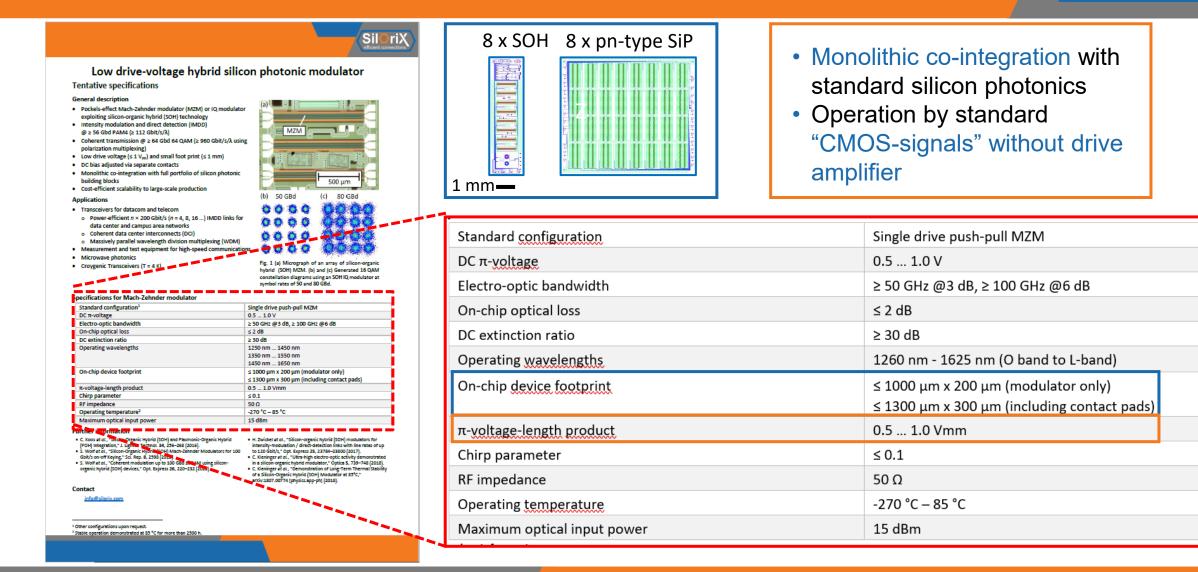




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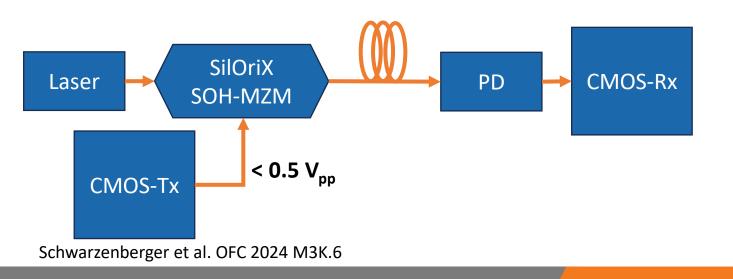
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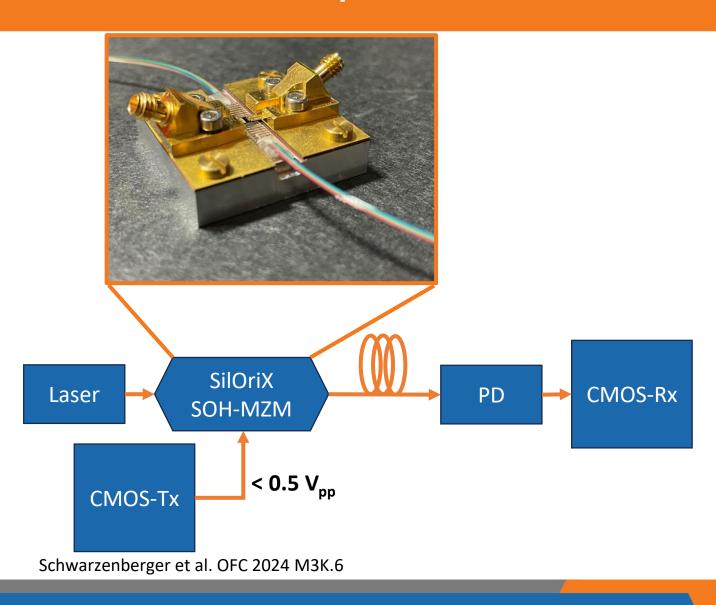
Driver-less operation





Driver-less operation

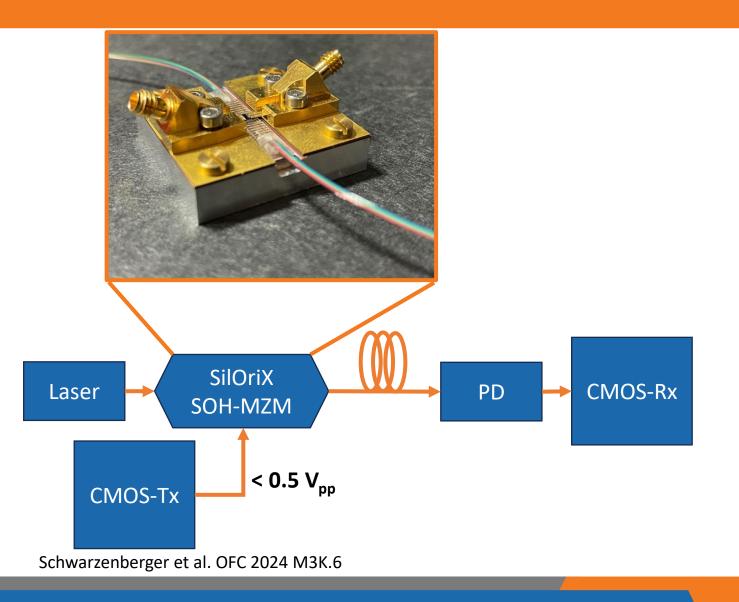




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Driver-less operation





- Fully packaged SOH-modulator utilizing SilOriX's proprietery organic electro-optic materials and PIC designs.
- 112 Gbit/s PAM4 data transmission
- Driver-less operation at CMOS-compatible voltage swings below 0.5 V

Long-term stable SOH modulators

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SilOriX

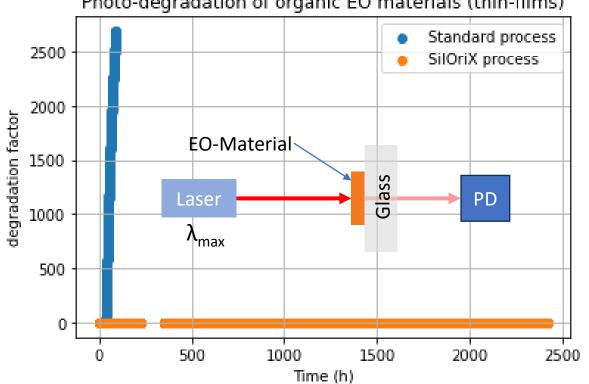
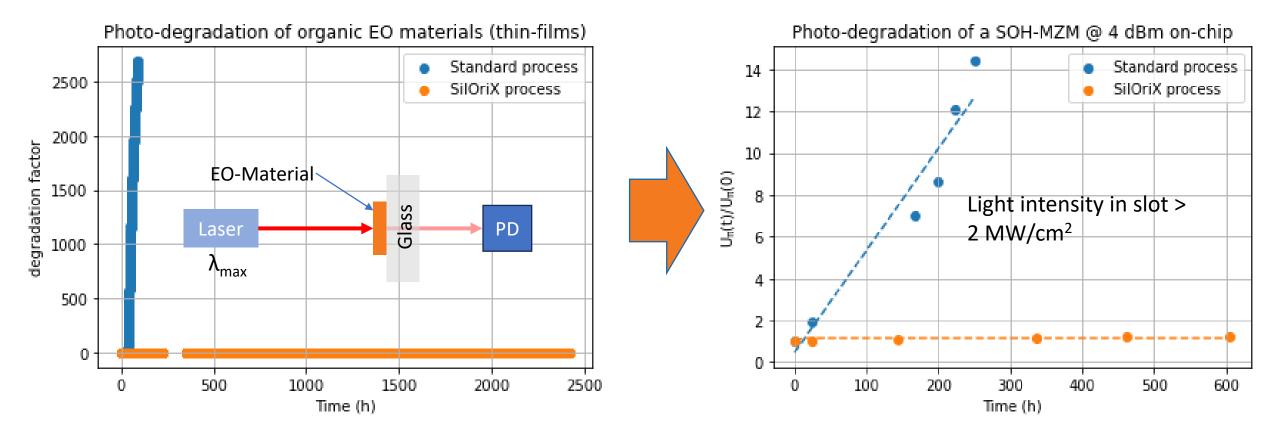


Photo-degradation of organic EO materials (thin-films)

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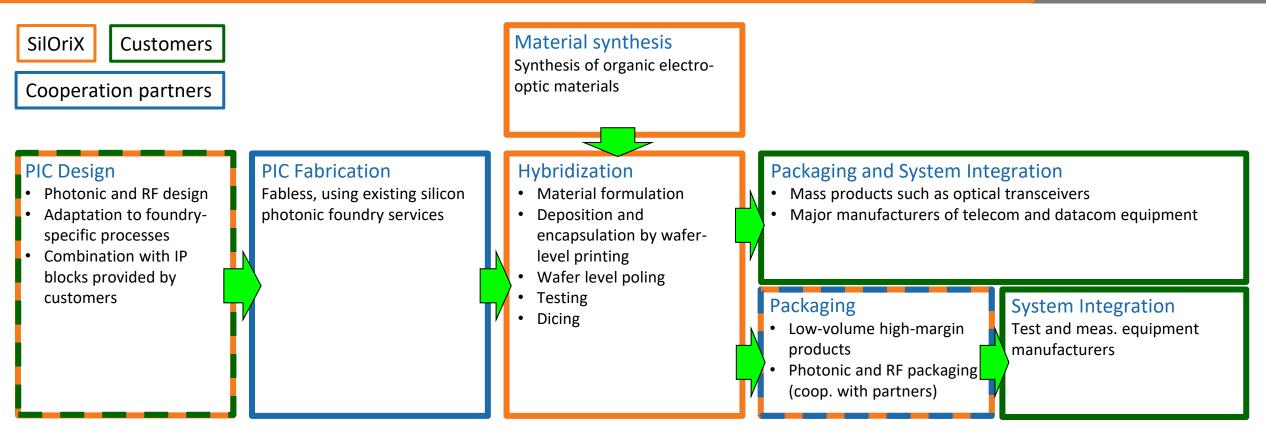
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Long-term stable SOH modulators



SilOriX

Value chain and product development



- Customized photonic integrated circuits (PIC) on a die level, for packaging and system integration by customers
- Customized packaged devices for high-margin niche applications
- PDK building blocks accessible through partner foundries
- Technology licensing for ultra-scale mass production by major transceiver manufacturers

In a nutshell



Silicon-organic hybrid electro-optic modulators with disruptive performance

Efficient

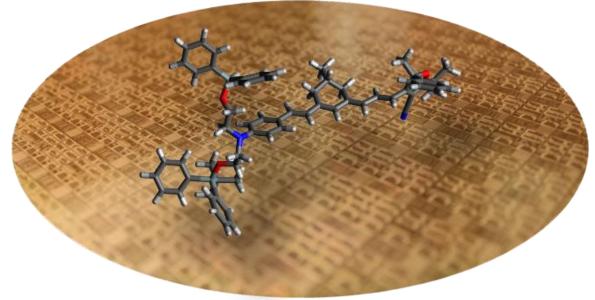
Sub-volt drive signals for ultra-low energy dissipation

Fast

Modulation at symbol rates of 190 GBd and beyond

Scalable

Monolithic back-end-of-line co-integration with established silicon photonics



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